

# DATA SHEET

## **BLT80** UHF power transistor

Product specification  
Supersedes data of May 1992

1996 May 09

# UHF power transistor

# BLT80

### FEATURES

- SMD encapsulation
- Gold metallization ensures excellent reliability.

### APPLICATIONS

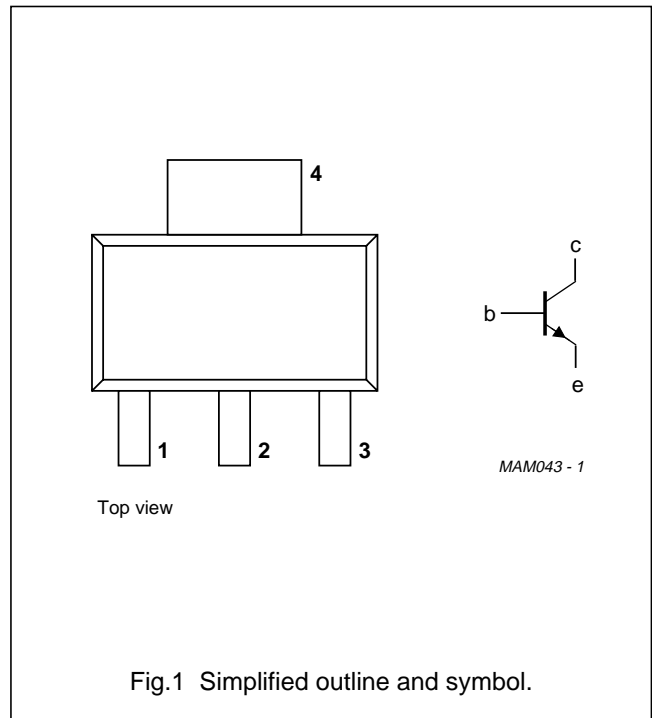
- Hand-held radio equipment in the 900 MHz communication band.

### DESCRIPTION

NPN silicon planar epitaxial transistor encapsulated in a plastic SOT223 SMD package.

### PINNING - SOT223

PIN	SYMBOL	DESCRIPTION
1	e	emitter
2	b	base
3	e	emitter
4	c	collector



### QUICK REFERENCE DATA

RF performance at  $T_s \leq 60 \text{ }^\circ\text{C}$  in a common emitter test circuit (see Fig.7).

MODE OF OPERATION	f (MHz)	V <sub>CE</sub> (V)	P <sub>L</sub> (W)	G <sub>p</sub> (dB)	$\eta_c$ (%)
CW, class-B narrow band	900	7.5	0.8	$\geq 6$	$\geq 60$

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**LIMITING VALUES**

In accordance with the Absolute Maximum Rating System (IEC 134).

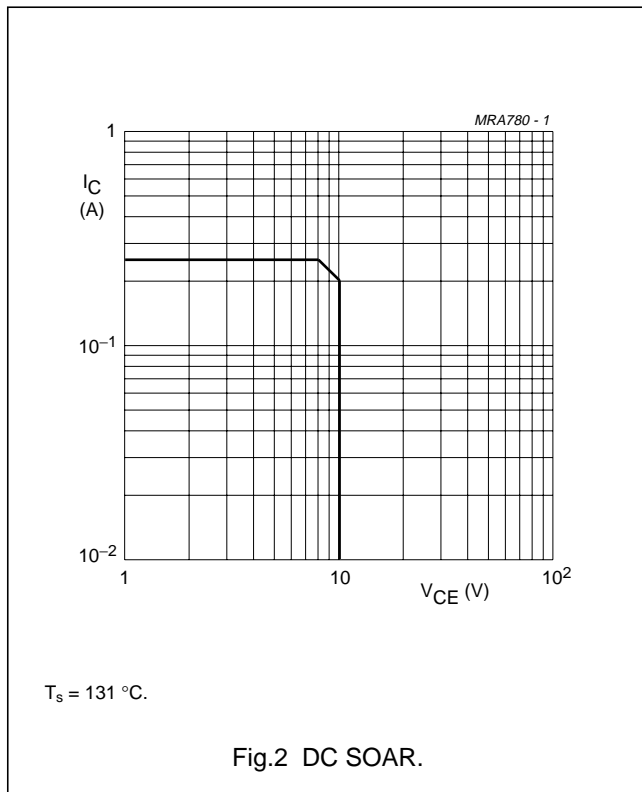
SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{CBO}$	collector-base voltage	open emitter	–	20	V
$V_{CEO}$	collector-emitter voltage	open base	–	10	V
$V_{EBO}$	emitter-base voltage	open collector	–	3	V
$I_C$	collector current (DC)		–	250	mA
$I_{C(AV)}$	average collector current		–	250	mA
$I_{CM}$	peak collector current	$f > 1$ MHz	–	750	mA
$P_{tot}$	total power dissipation	$T_s = 131$ °C; note 1	–	2	W
$T_{stg}$	storage temperature		–65	+150	°C
$T_j$	operating junction temperature		–	175	°C

**THERMAL CHARACTERISTICS**

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	$P_{tot} = 2$ W; $T_s = 131$ °C; note 1	22	K/W
$R_{th\ j-a}$	thermal resistance from junction to ambient	$P_{tot} = 2$ W; $T_{amb} = 25$ °C; note 2	85	K/W

**Note to the “Limiting values” and “Thermal characteristics”**

- $T_s$  is the temperature at the soldering point of the collector pin.
- Transistor mounted on a printed-circuit board measuring  $40 \times 40 \times 1$  mm, collector pad  $35 \times 17$  mm.



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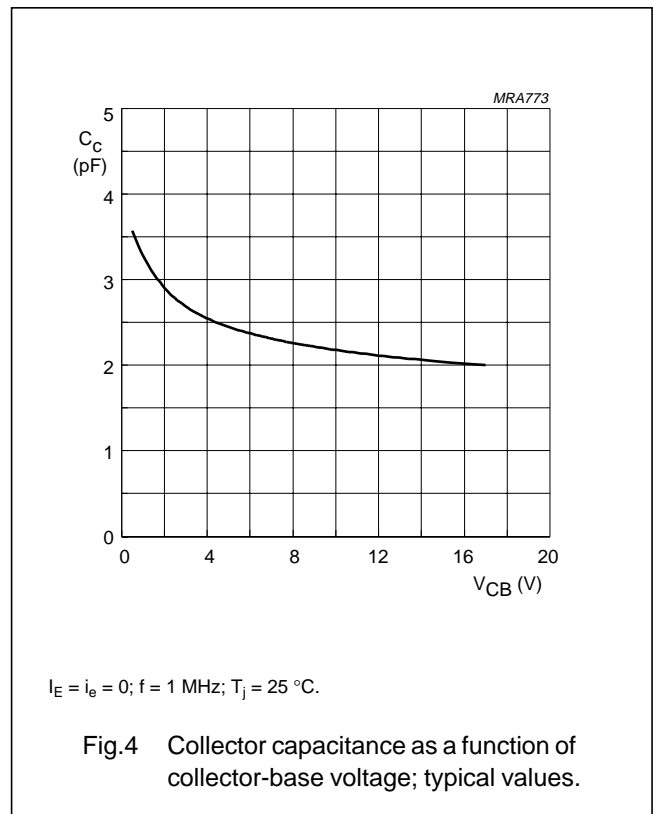
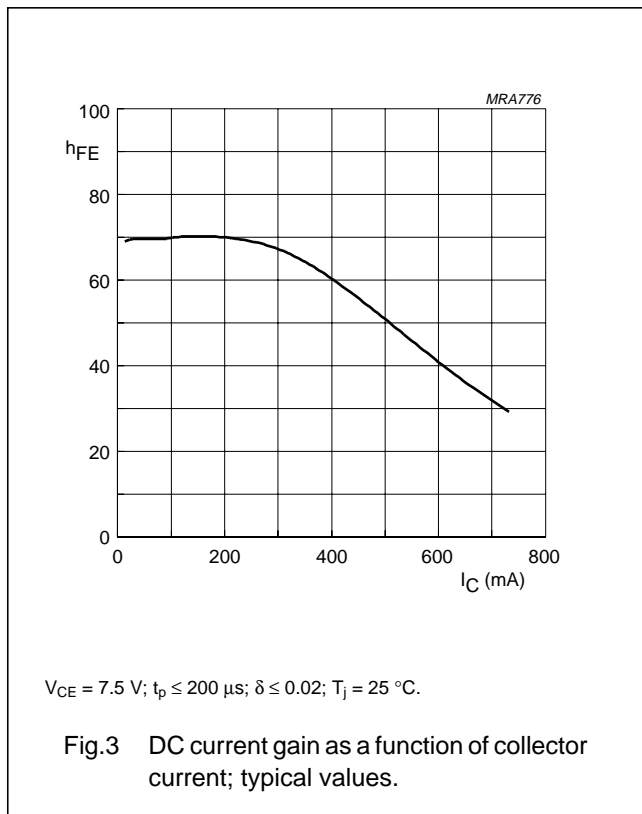
**CHARACTERISTICS**

$T_j = 25\text{ }^\circ\text{C}$  unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; $I_C = 2.5\text{ mA}$	20	–	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	open base; $I_C = 5\text{ mA}$	10	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	open collector; $I_E = 0.5\text{ mA}$	3	–	V
$I_{CES}$	collector leakage current	$V_{CE} = 10\text{ V}$ ; $V_{BE} = 0$	–	0.1	mA
$h_{FE}$	DC current gain	$V_{CE} = 5\text{ V}$ ; $I_C = 150\text{ mA}$ ; note 1; see Fig.3	25	–	
$C_c$	collector capacitance	$V_{CB} = 7.5\text{ V}$ ; $I_E = i_e = 0$ ; $f = 1\text{ MHz}$ ; see Fig.4	–	3.5	pF
$C_{re}$	feedback capacitance	$V_{CE} = 7.5\text{ V}$ ; $I_C = 0$ ; $f = 1\text{ MHz}$	–	2.5	pF

**Note**

1. Measured under pulsed conditions:  $t_p \leq 200\text{ }\mu\text{s}$ ;  $\delta \leq 0.02$ .



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**APPLICATION INFORMATION**

RF performance at  $T_s \leq 60\text{ }^\circ\text{C}$  in a common emitter test circuit (see note 1 and Fig.7).

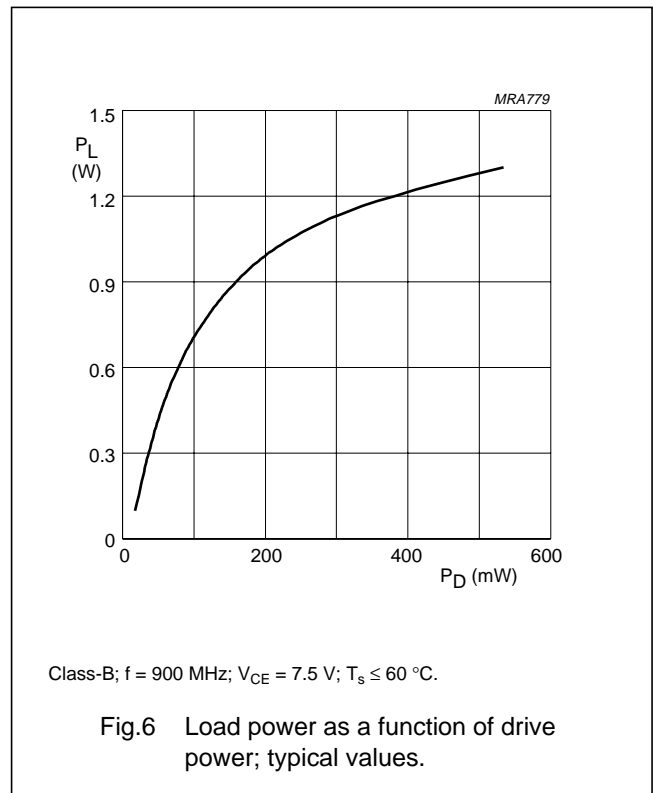
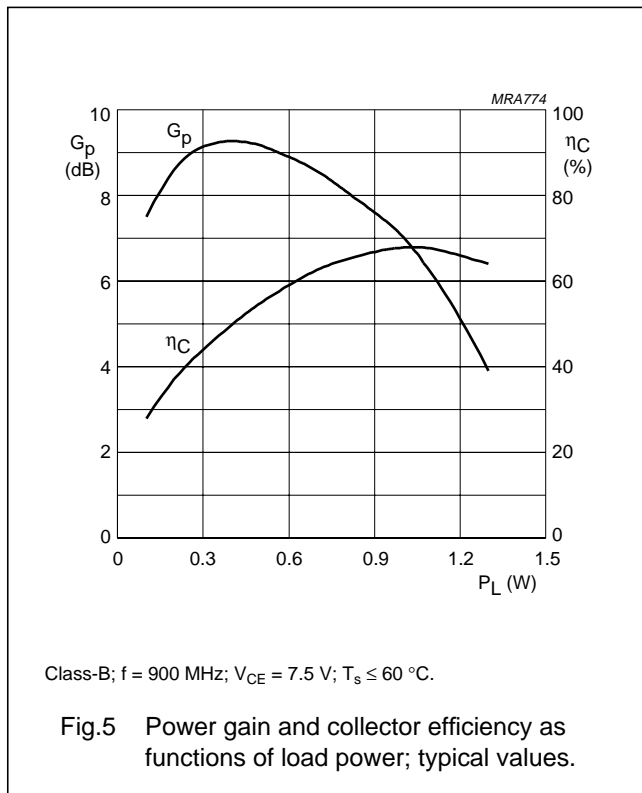
MODE OF OPERATION	f (MHz)	V <sub>CE</sub> (V)	P <sub>L</sub> (W)	G <sub>p</sub> (dB)	$\eta_c$ (%)
CW, class-B narrow band	900	7.5	0.8	$\geq 6$ typ. 8	$\geq 60$ typ. 67

**Note**

1.  $T_s$  is the temperature at the soldering point of the collector pin.

**Ruggedness in class-AB operation**

The BLT80 is capable of withstanding a load mismatch corresponding to VSWR = 50 : 1 through all phases under the following conditions: f = 900 MHz; V<sub>CE</sub> = 9 V; P<sub>L</sub> = 0.8 W;  $T_s \leq 60\text{ }^\circ\text{C}$ .



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## Test circuit information

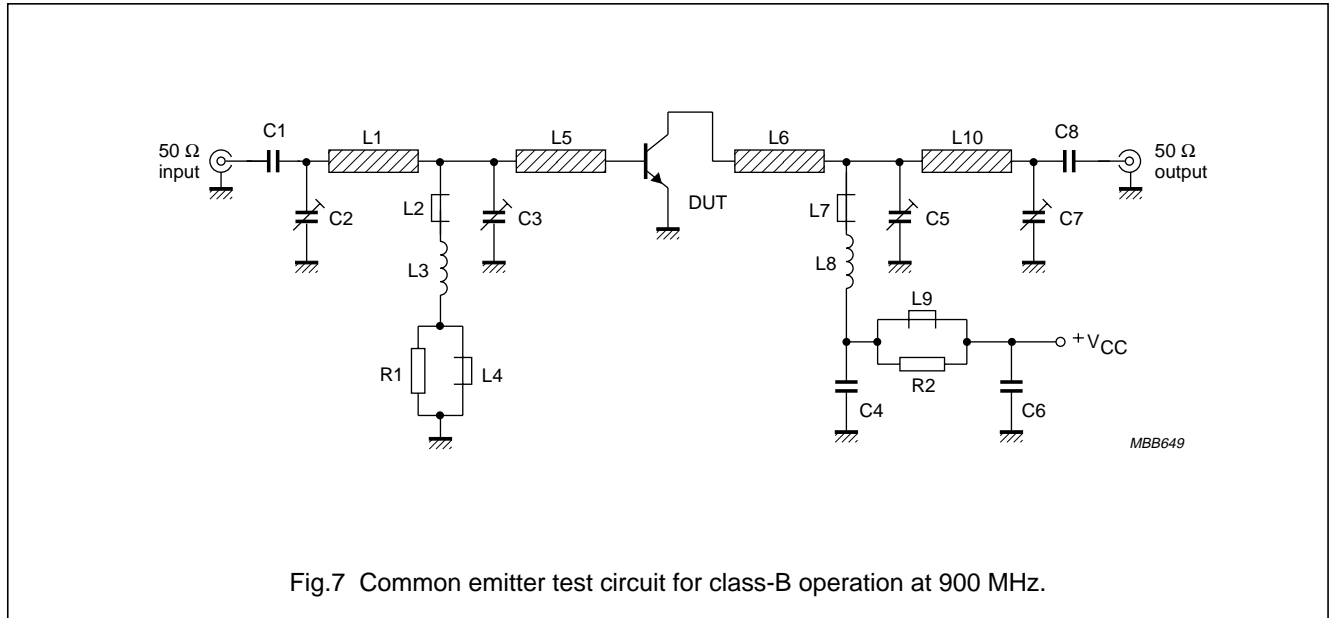


Fig.7 Common emitter test circuit for class-B operation at 900 MHz.

## List of components used in test circuit (see Figs 7 and 8)

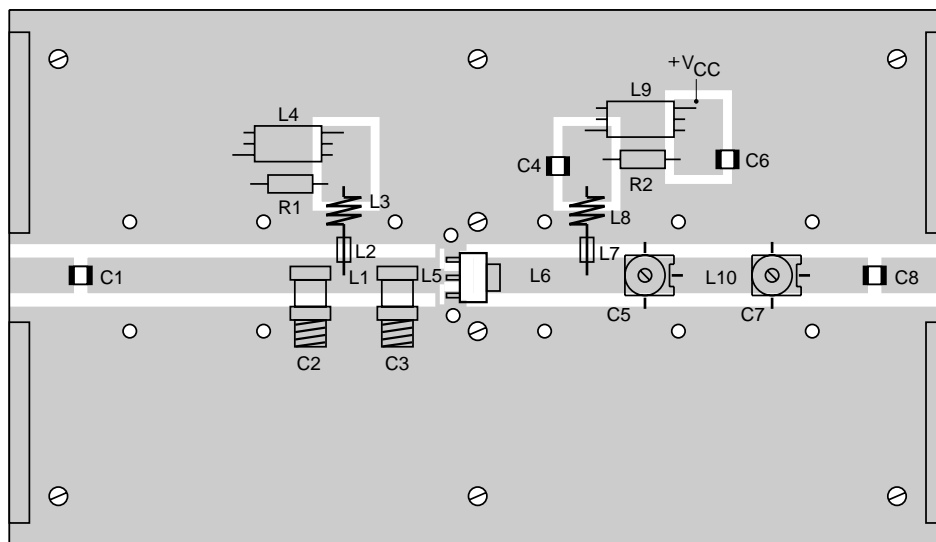
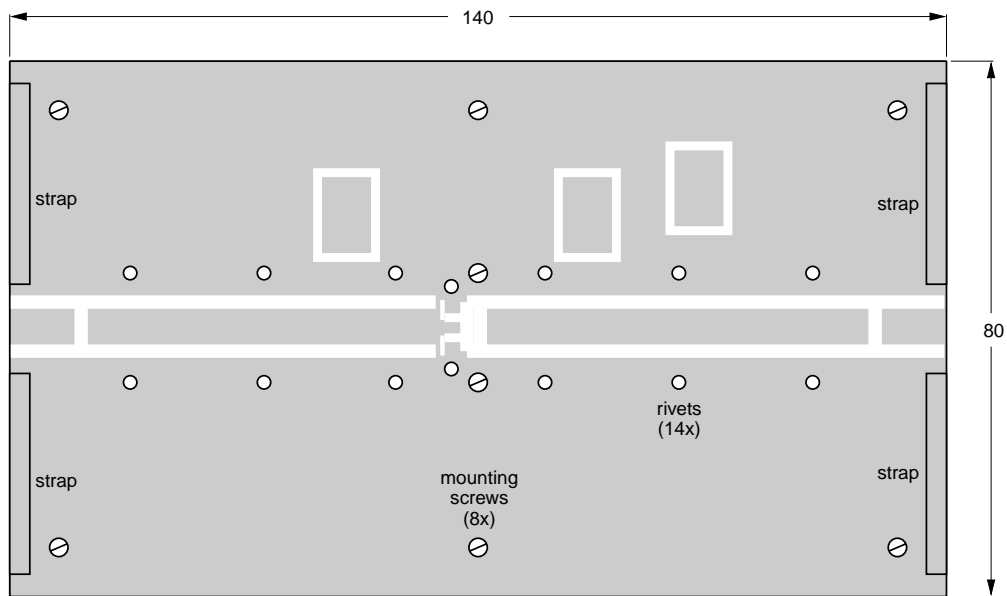
COMPONENT	DESCRIPTION	VALUE	DIMENSIONS	CATALOGUE No.
C1, C8	multilayer ceramic chip capacitor; note 1	100 pF		
C2, C3	type 9105 Voltronix KM10 trimmer	0.6 to 10 pF		
C4	multilayer ceramic chip capacitor; note 1	220 pF		
C5, C7	film dielectric trimmer	1.4 to 5.5 pF		2222 809 09001
C6	multilayer ceramic chip capacitor; note 1	1 nF		
L1	stripline; note 2	50 Ω	length 13 mm width 4.85 mm	
L2, L7	1 turn 0.4 mm copper wire on grade 3B core			4330 030 32221
L3, L8	6 turns enamelled 0.8 mm copper wire		internal dia. 3 mm	
L4, L9	grade 3B Ferroxcube wideband HF choke			4312 020 36640
L5	stripline; note 2	50 Ω	length 8.4 mm width 4.85 mm	
L6	stripline; note 2	50 Ω	length 20 mm width 4.85 mm	
L10	stripline; note 2	50 Ω	length 21 mm width 4.85 mm	
R1, R2	metal film resistor	10 Ω, 0.25 W		

## Notes

- American Technical Ceramics type 100A or capacitor of same quality.
- The striplines are on a double copper-clad printed-circuit board, with PTFE fibre-glass dielectric ( $\epsilon_r = 2.2$ ); thickness  $\frac{1}{16}$ "; thickness of the copper sheet 35  $\mu\text{m}$ .

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MBB648

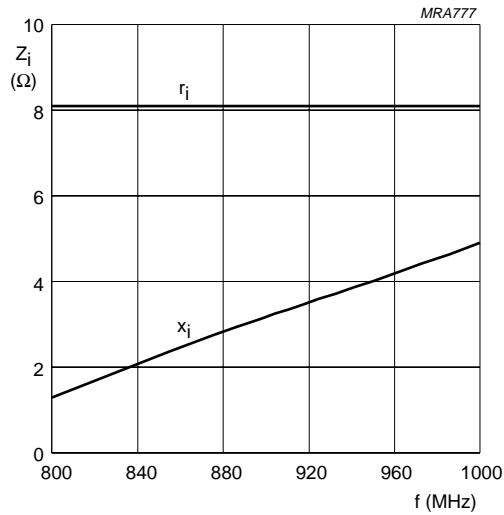
Dimensions in mm.

The components are situated on one side of the copper-clad PTFE fibre-glass board, the other side is unetched and serves as a ground plane. Earth connections from the component side to the ground plane are made by means of fixing screws and copper foil straps under the emitter leads.

Fig.8 Printed-circuit board and component lay-out for 900 MHz class-B test circuit in Fig.7.

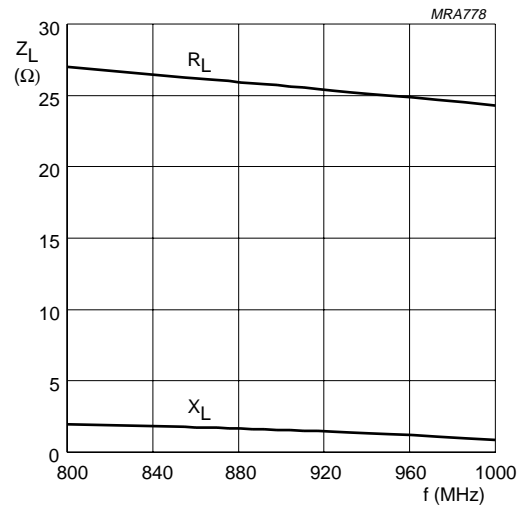
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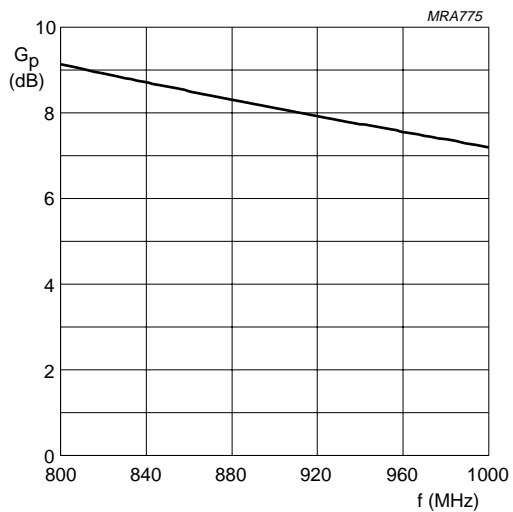
Class-B;  $V_{CE} = 7.5 \text{ V}$ ;  $P_L = 0.8 \text{ W}$ ;  $T_s \leq 60 \text{ }^\circ\text{C}$ .

Fig.9 Input impedance as a function of frequency (series components); typical values.



Class-B;  $V_{CE} = 7.5 \text{ V}$ ;  $P_L = 0.8 \text{ W}$ ;  $T_s \leq 60 \text{ }^\circ\text{C}$ .

Fig.10 Load impedance as a function of frequency (series components); typical values.



Class-B;  $V_{CE} = 7.5 \text{ V}$ ;  $P_L = 0.8 \text{ W}$ ;  $T_s \leq 60 \text{ }^\circ\text{C}$ .

Fig.11 Power gain as a function of frequency; typical values.

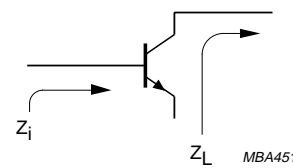


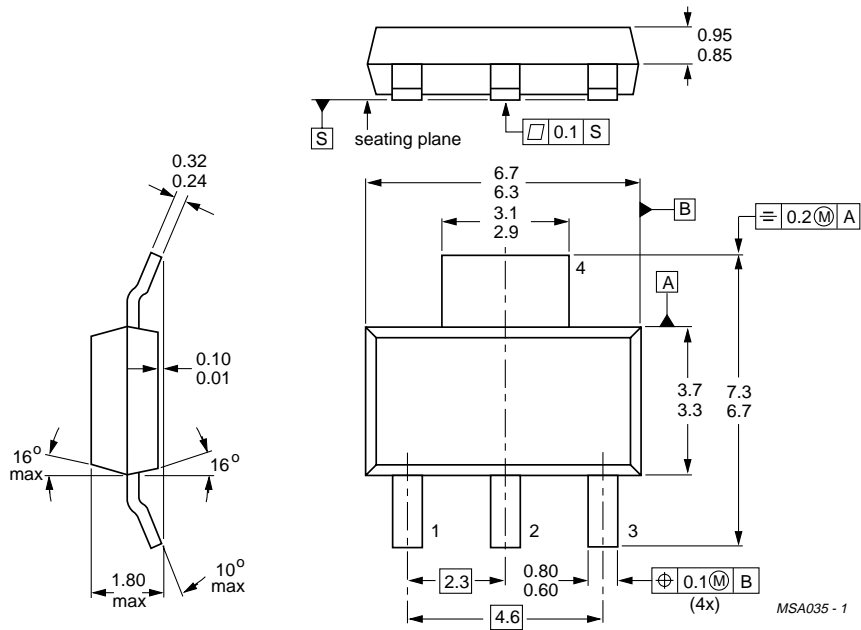
Fig.12 Definition of transistor impedance.



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PACKAGE OUTLINE



Dimensions in mm.

Fig.13 SOT223.

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**DEFINITIONS**

<b>Data Sheet Status</b>	
Objective specification	This data sheet contains target or goal specifications for product development.
Preliminary specification	This data sheet contains preliminary data; supplementary data may be published later.
Product specification	This data sheet contains final product specifications.
<b>Limiting values</b>	
Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.	
<b>Application information</b>	
Where application information is given, it is advisory and does not form part of the specification.	

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